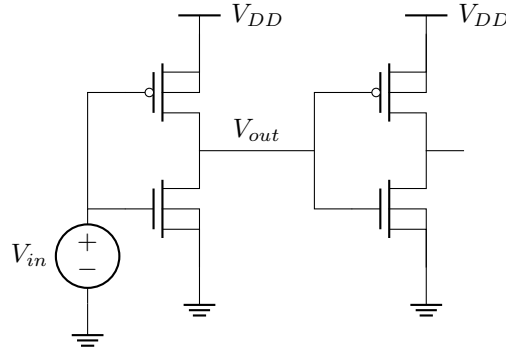


EC 5311 Digital IC Design: Assignment 3
CMOS inverter - transient characteristics

$$\begin{aligned} V_{Tn} = 0.7, \quad \mu_n = 0.025 \text{ m}^2/\text{V} \cdot \text{s}, \quad C_{oxn} = 0.00834 \text{ F/m}^2, \quad v_{satn} = 8e4 \text{ m/s}, \quad \lambda_n = 0.2 \\ |V_{Tp}| = 0.7, \quad \mu_p = 0.009 \text{ m}^2/\text{V} \cdot \text{s}, \quad C_{oxp} = 0.00816 \text{ F/m}^2, \quad v_{satp} = 3e4 \text{ m/s}, \quad \lambda_p = 0.2. \end{aligned}$$

1. Consider the static CMOS inverter shown below. It drives another identical inverter. The input V_{in} is a pulse between 0 and V_{DD} , with a rise and fall time equal to 5 ps and a pulse width of 250 ps. The output is V_{out} .



- (a) Set $V_{DD} = 1.8\text{V}$. Assume that $L_n = L_p = 0.15 \mu\text{m}$ and $W_n = 0.42 \mu\text{m}$. Obtain the delay for $W_p = 0.42 \mu\text{m}, 0.84 \mu\text{m}, 1.26 \mu\text{m}$.
- (b) Set W_p so that delay is minimised. Plot the delay as a function of V_{DD} for $V_{DD} = 1\text{V}$ to 1.8V in steps of 0.1V . How does it compare with analytical estimates?
- (c) Plot the measured and estimated energy-delay product as a function of V_{DD} . What is the optimum V_{DD} ?